

Please insert the following new paragraph beginning at page 7, line 10, with the following:

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FIG. 5 is a process flowchart of an alternative process similar to the process shown in FIG. 4, with the exception that the step of sputtering the encapsulation layer is followed by masking and etching of the encapsulation and bottom electrode layers, followed by a second RTA anneal.

REMARKS

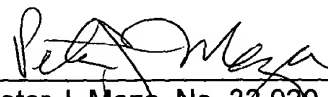
A description of an omitted description of FIG. 5 and two other minor punctuation edits are presented by this amendment. Support for this amendment is found in FIG. 5 itself, and also in the specification at page 13, lines 28-33. No new matter is included in this amendment.

Attached hereto is a marked-up version of the changes made to the specification. The attached page is captioned "Version with Markings to Show Changes Made."

No fee is believed due for this submittal. However, any fee deficiency associated with this submittal may be charged to Deposit Account No. 50-1123.

Respectfully submitted,

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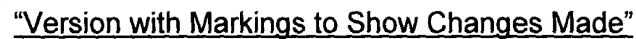


Figure 4 is a process flowchart illustrating an alternative process wherein the top electrode layer is deposited following a first RTA anneal, and a second RTA anneal is performed after etching of the PZT and deposition of an encapsulation layer[.]; and

[illegible]